High Voltage Transistors NPN Silicon

MMBT5550L, MMBT5551L

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|------------------|-----------------|----------|
| Collector - Emitter Voltage MMBT5550 MMBT5551 | V _{CEO} | 140 160 | Vdc |
| Collector – Base Voltage MMBT5550 MMBT5551 | V _{CBO} | 160 180 | Vdc |
| Emitter - Base Voltage | V _{EBO} | 6.0 | Vdc |
| Collector Current - Continuous | I _C | 600 | mAdc |
| Electrostatic Discharge Human Body Model Machine Model | ESD | > 8000 > 400 | V |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------------------------|-------------|-------------|
| Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate Above 25°C | P _D | 225 1.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 556 | °C/W |
| Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate Above 25°C | P _D | 300 2.4 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 417 | °C/W |
| Junction and Storage Temperature | T _J , T _{stg} | -55 to +150 | °C |

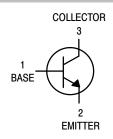
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

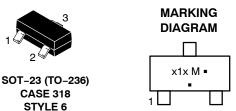
- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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x1x = Device Code

M1F = MMBT5550LT

G1 = MMBT5551LT

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------------------------|---------------------|-------------------------|
| MMBT5550LT1G, NSVMMBT5550LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| MMBT5550LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| MMBT5551LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SMMBT5551LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| MMBT5551LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| SMMBT5551LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | | Symbol | Min | Max | Unit |
|--|--|-----------------------|----------------------------------|---------------------------|--------------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$ | MMBT5550 MMBT5551 | V _{(BR)CEO} | 140 160 | - - | Vdc |
| Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$) | MMBT5550 MMBT5551 | V _(BR) CBO | 160 180 | - - | Vdc |
| Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0) | | V _{(BR)EBO} | 6.0 | - | Vdc |
| Collector Cutoff Current | MMBT5550 MMBT5551 MMBT5550 MMBT5551 | I _{CBO} | - - - | 100 50 100 50 | nAdc μAdc |
| Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0) | | I _{EBO} | - | 50 | nAdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain $(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ | MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551 | h _{FE} | 60 80 60 80 20 30 | - 250 250 - - | - |
| Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$) | Both Types MMBT5550 MMBT5551 | V _{CE(sat)} | - - - | 0.15 0.25 0.20 | Vdc |
| Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$) | Both Types MMBT5550 MMBT5551 | V _{BE(sat)} | - - - | 1.0 1.2 1.0 | Vdc |
| Collector Emitter Cut-off (V _{CB} = 10 V) (V _{CB} = 75 V) | Both Types | I _{CES} | - - | 50 100 | nA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

TYPICAL CHARACTERISTICS

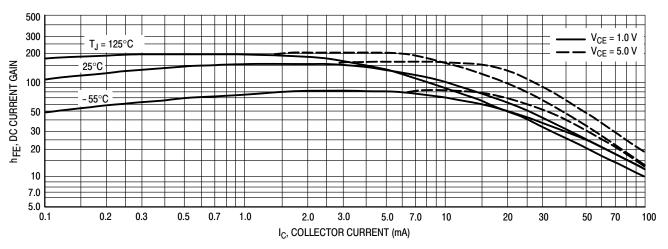


Figure 1. DC Current Gain

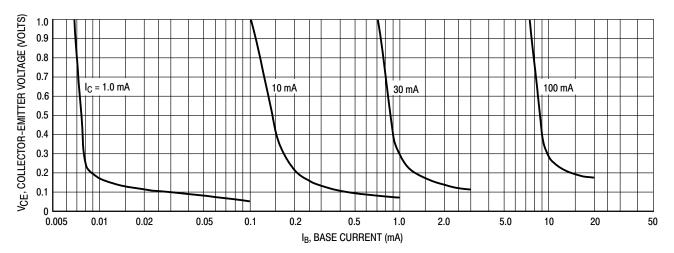


Figure 2. Collector Saturation Region

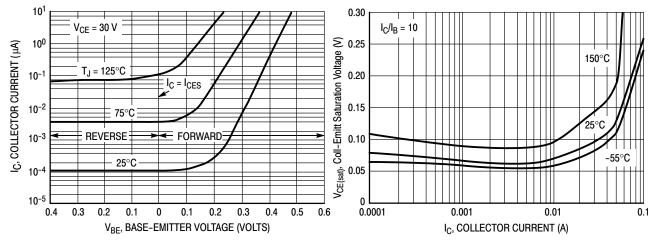
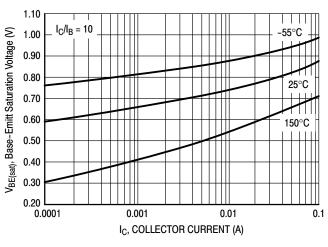


Figure 3. Collector Cut-Off Region

Figure 4. V_{CE(sat)}

TYPICAL CHARACTERISTICS



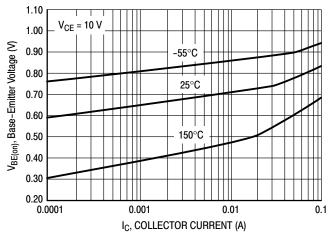
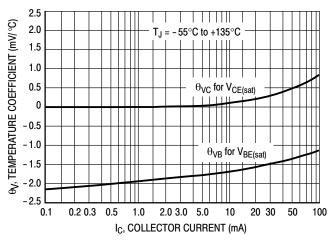


Figure 5. V_{BE(sat)}

Figure 6. V_{BE(on)}



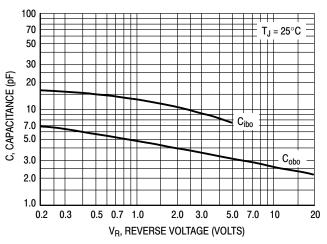
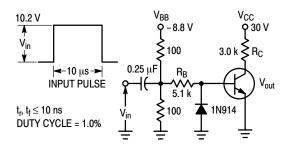


Figure 7. Temperature Coefficients

Figure 8. Capacitances



Values Shown are for I_C @ 10 mA

Figure 9. Switching Time Test Circuit

TYPICAL CHARACTERISTICS

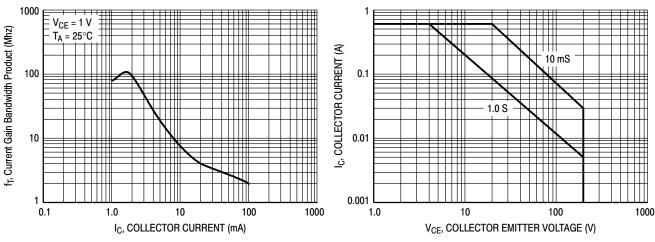


Figure 10. Current Gain Bandwidth Product



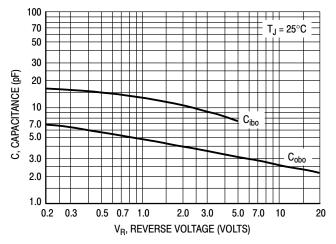


Figure 12. Capacitances

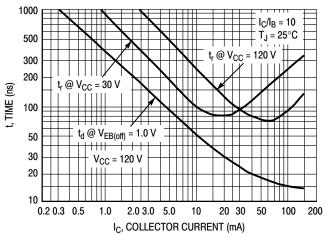


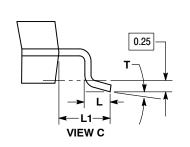
Figure 13. Turn-On Time

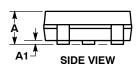


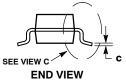
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

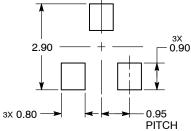
SCALE 4:1 D - 3X b **TOP VIEW**







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

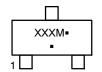
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NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| С | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| е | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | O٥ | | 10° | O۰ | | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | ı | |
|---|---|---|--|------------------|------------------|
| STYLE 9: | STYLE 10: | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: | STYLE 13: | STYLE 14: |
| PIN 1. ANODE | PIN 1. DRAIN | | PIN 1. CATHODE | PIN 1. SOURCE | PIN 1. CATHODE |
| 2. ANODE | 2. SOURCE | | 2. CATHODE | 2. DRAIN | 2. GATE |
| 3. CATHODE | 3. GATE | | 3. ANODE | 3. GATE | 3. ANODE |
| STYLE 15: | STYLE 16: | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: | STYLE 19: | STYLE 20: |
| PIN 1. GATE | PIN 1. ANODE | | PIN 1. NO CONNECTION | I PIN 1. CATHODE | PIN 1. CATHODE |
| 2. CATHODE | 2. CATHODE | | 2. CATHODE | 2. ANODE | 2. ANODE |
| 3. ANODE | 3. CATHODE | | 3. ANODE | 3. CATHODE-ANODE | 3. GATE |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: | STYLE 25: | STYLE 26: |
| PIN 1. GATE | PIN 1. RETURN | PIN 1. ANODE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE |
| 2. SOURCE | 2. OUTPUT | 2. ANODE | 2. DRAIN | 2. CATHODE | 2. ANODE |
| 3. DRAIN | 3. INPUT | 3. CATHODE | 3. SOURCE | 3. GATE | 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE | | | | |

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| DESCRIPTION: | SOT-23 (TO-236) | | PAGE 1 OF 1 | |

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